

SILICON POWER TRANSISTOR 2SD1695

NPN SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR LOW-FREQUENCY POWER AMPLIFIERS AND LOW-SPEED SWITCHING

The 2SD1695 is a Darlington connection transistor and incorporates a dumper diode between the collector and emitter and a constant voltage diode and protection elements between the collector and base. This transistor is ideal for drives in solenoid and actuators.

FEATURES

• On-chip protection elements enable time and cost reduction.

C to E: Dumper diode C to B: Constant diode

· Low collector saturation voltage

QUALITY GRADES

Standard

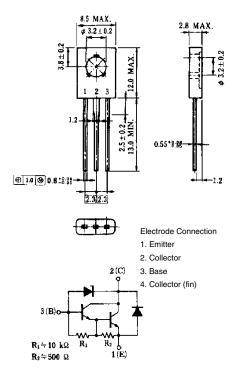
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ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{СВО}	31 ±4	٧
Collector to emitter voltage	VCEO	31 ±4	٧
Emitter to base voltage	V _{EBO}	8.0	٧
Collector current (DC)	Ic(DC)	±2.0	Α
Collector current (pulse)	IC(pulse)*	±3.0	Α
Base current (DC)	I _{B(DC)}	0.2	Α
Total power dissipation	P⊤ (Ta = 25°C)	1.3	W
Total power dissipation	P _T (Tc = 25°C)	10	W
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

^{*} PW \leq 10 ms, duty cycle \leq 50%

PACKAGE DRAWING (UNIT: mm)



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

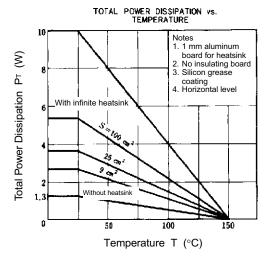
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to base voltage VcBo Collector to emitter voltage VcEo		Ic = 1.0 mA, IE = 0	27	31	35	V
		Ic = 10 mA, R _{BE} = ∞	27	31	35	V
Collector cutoff current	Ісво	Vcb = 20 V, IE = 0			10	μΑ
DC current gain	h _{FE1} *	Vce = 2.0 V, Ic = 0.5 A	1,000			
DC current gain	h _{FE2} *	VcE = 2.0 V, Ic = 1.0 A	2,000		30,000	
Collector saturation voltage	V _{CE(sat)} *	Ic = 1.0 A, I _B = 1.0 mA		0.9	1.2	V
Base saturation voltage	V _{BE(sat)} *	Ic = 1.0 A, I _B = 1.0 mA		1.6	2.0	V
Turn-on time	ton	Ic = 1.0 A, I _{B1} = $-I_{B2}$ = 5.0 mA R _L = 20 Ω , Vcc \cong 20 V		0.5		μs
Storage time	t stg			3.0		μs
Fall time	tf			1.0		μs

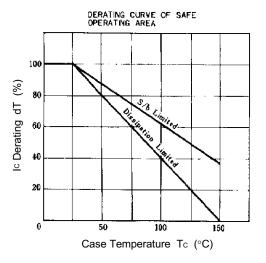
^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

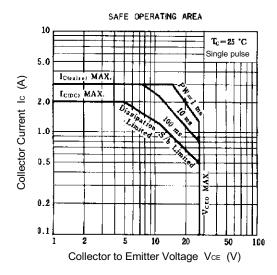
hfe2 CLASSIFICATION

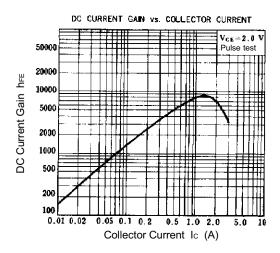
Marking	М	L	K
h _{FE2}	2,000 to 5,000	4,000 to 10,000	8,000 to 30,000

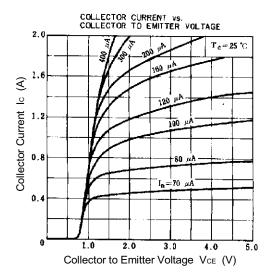
TYPICAL CHARACTERISTICS (Ta = 25°C)

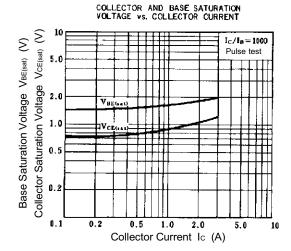












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